

IR2101(S)/IR2102(S) &(PbF)

HIGH AND LOW SIDE DRIVER Product Summary

Features

- Floating channel designed for bootstrap operation
Fully operational to +600V
Tolerant to negative transient voltage
dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout
- 3.3V, 5V, and 15V logic input compatible
- Matched propagation delay for both channels
- Outputs in phase with inputs (IR2101) or out of phase with inputs (IR2102)
- Also available LEAD-FREE

V_{OFFSET}	600V max.
$I_{\text{O+/-}}$	130 mA / 270 mA
V_{OUT}	10 - 20V
$t_{\text{on/off (typ.)}}$	160 & 150 ns
Delay Matching	50 ns

Description

The IR2101(S)/IR2102(S) are high voltage, high speed power MOSFET and IGBT drivers with independent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.

Packages

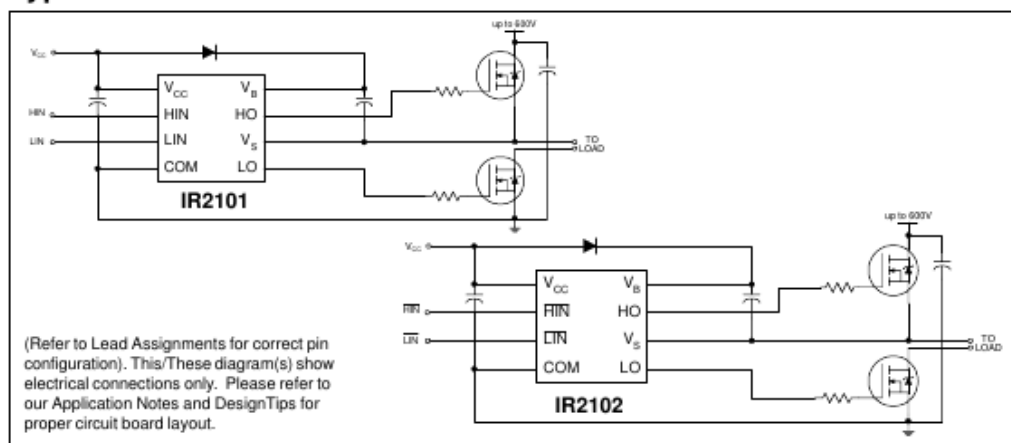


8-Lead SOIC
IR2101S/IR2102S



8-Lead PDIP
IR2101/IR2102

Typical Connection



IR2101(S)/IR2102(S) & (PbF)

International
IR Rectifier

Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units
V _B	High side floating supply voltage	-0.3	625	V
V _S	High side floating supply offset voltage	V _B - 25	V _B + 0.3	
V _{HO}	High side floating output voltage	V _S - 0.3	V _B + 0.3	
V _{CC}	Low side and logic fixed supply voltage	-0.3	25	
V _{LO}	Low side output voltage	-0.3	V _{CC} + 0.3	
V _{IN}	Logic input voltage (HIN & LIN)	-0.3	V _{CC} + 0.3	
dV _S /dt	Allowable offset supply voltage transient	—	50	V/ns
P _D	Package power dissipation @ T _A ≤ +25°C	(8 lead PDIP) —	1.0	W
		(8 lead SOIC) —	0.625	
R _{thJA}	Thermal resistance, junction to ambient	(8 lead PDIP) —	125	°C/W
		(8 lead SOIC) —	200	
T _J	Junction temperature	—	150	°C
T _S	Storage temperature	-55	150	
T _L	Lead temperature (soldering, 10 seconds)	—	300	

Recommended Operating Conditions

The input/output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The V_S offset rating is tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
V _B	High side floating supply absolute voltage	V _S + 10	V _S + 20	V
V _S	High side floating supply offset voltage	Note 1	600	
V _{HO}	High side floating output voltage	V _S	V _B	
V _{CC}	Low side and logic fixed supply voltage	10	20	
V _{LO}	Low side output voltage	0	V _{CC}	
V _{IN}	Logic input voltage (HIN & LIN) (IR2101) & (HIN & LIN) (IR2102)	0	V _{CC}	
T _A	Ambient temperature	-40	125	°C

Note 1: Logic operational for V_S of -5 to +600V. Logic state held for V_S of -5V to -V_{BS}. (Please refer to the Design Tip DT97-3 for more details).

